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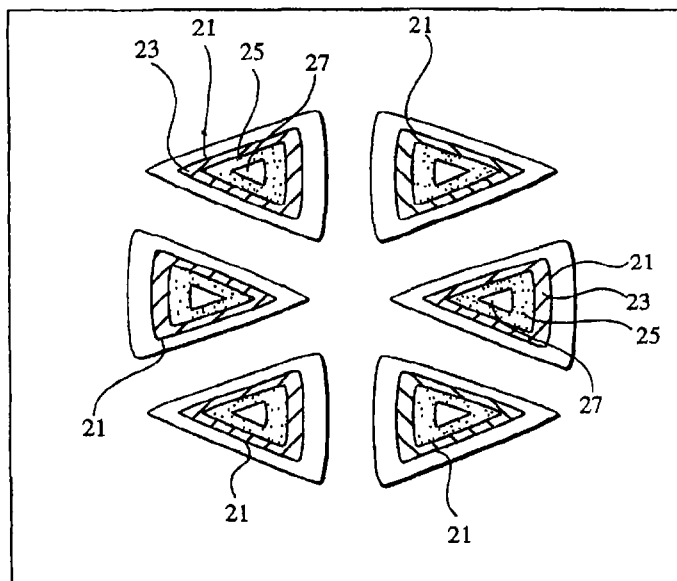
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4) Title: A NOVEL CHROMELESS ALTERNATING RETICLE FOR PRODUCING SEMICONDUCTOR DEVICE FEATURES



(57) **Abstract:** An alternating phase shift reticle for a capacitor layout scheme for a memory device and a method for its fabrication are disclosed. The alternating phase shift mask has regions of 0 and 180 degree phase shifts arranged in a way such that all sides of each region corresponding to a given phase shift value are bounded by areas corresponding to an opposite phase shift value. The reticle can be used to produce densely packed capacitor features, in which the variance between the actual exposure pattern and the desired exposure pattern is reduced.

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